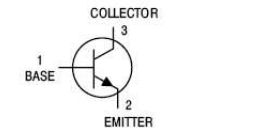
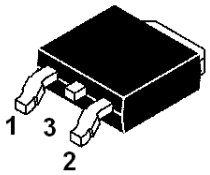
Power Transistor 2SD1760

FEATURES

- Low $V_{CE(sat)}$.
  $V_{CE(sat)}$=0.5V(Typ.)
  (I_C/I_B=2A/0.2A)
- Complements the 2SB1184.

Lead-free





TO-252

APPLICATIONS

- Epitaxial planar type.
- NPN silicon transistor.

MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Volage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current(DC)	3	A
I_{CP}	Collector Current(Pulse)	4.5	A
I_B	Base Current	1	A
P_C	Collector Power Dissipation	1.5	W
T_j , T_{stg}	Junction and Storage temperature range	-55 to +150	℃

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ELECTRICAL CHARACTERISTICS@ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	I_C=50uA,I_E=0	60			V
Collector-emitter breakdown voltage	V_{CEO}	I_C=1mA,I_B=0	50			V
Emitter-base breakdown voltage	V_{EBO}	I_E=50uA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0			1.0	uA
Emitter cut-off current	I_{EBO}	V_{EBO}=4V,I_C=0			1.0	uA
DC current gain	h_{FE}	V_{CE}=3V,I_C=0.5A	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B =2A/0.2A		0.5	1.0	V
Transition frequency	f_T	V_{CE}=5V,I_E=-500mA f=30MHz		90		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz		40		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

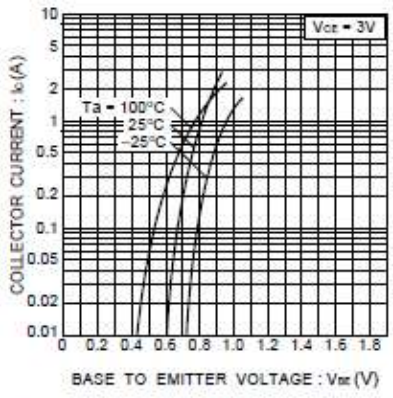

Fig.1 Grounded emitter propagation characteristics

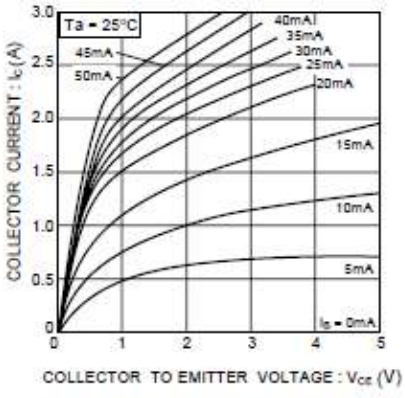

Fig.2 Grounded emitter output characteristics (I)

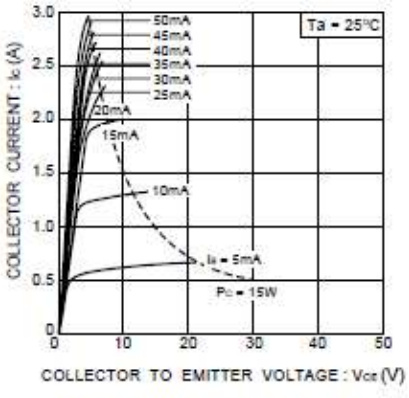

Fig.3 Grounded-emitter output characteristics(II)

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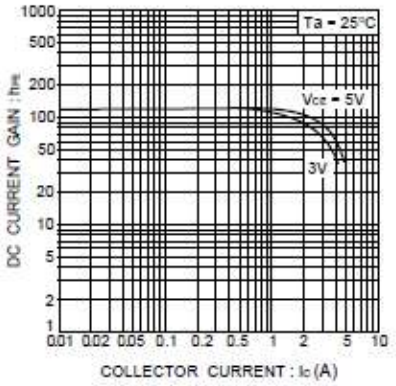

Fig.4 DC current gain vs. collector current(I)

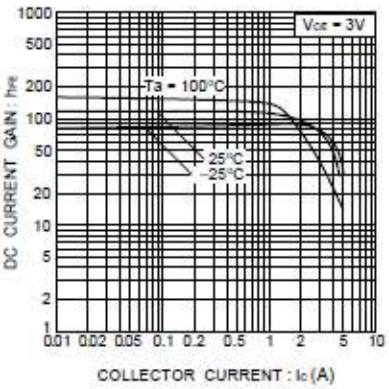

Fig.5 DC current gain vs. collector curren(II)

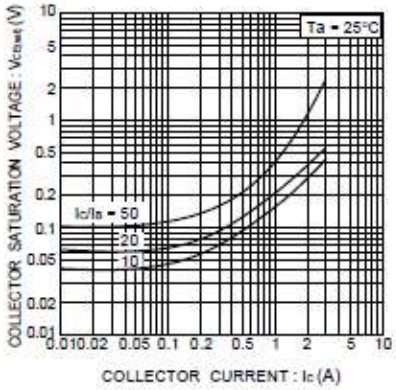

Fig.6 Collector-emitter saturation voltage vs. collector current

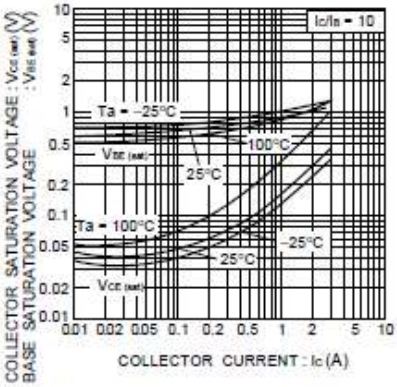

Fig.7 Collector-emitter saturation voltage vs. collector current
Base-emitter saturation voltage vs. collector current

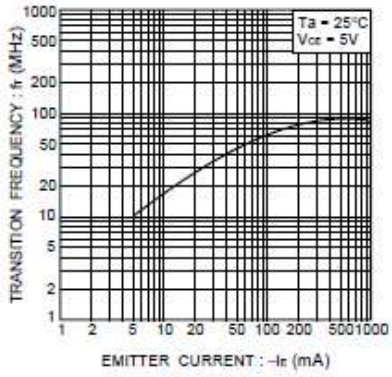

Fig.8 Gain bandwidth product vs. emitter current

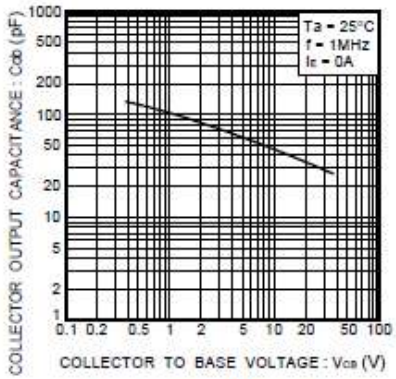

Fig.9 Collector output capacitance vs. collector-base voltage

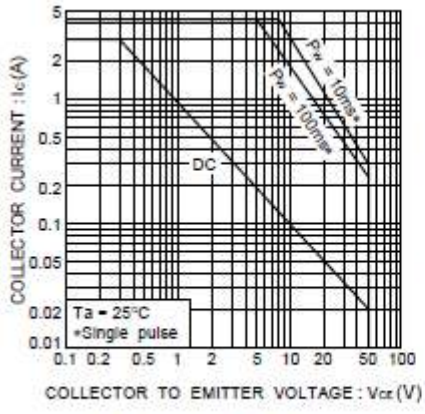

Fig.10 Safe operating area

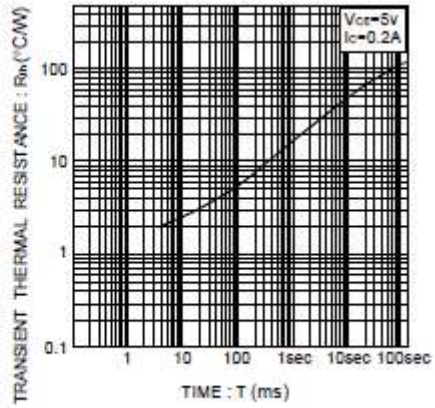

Fig.11 Transient thermal resistance

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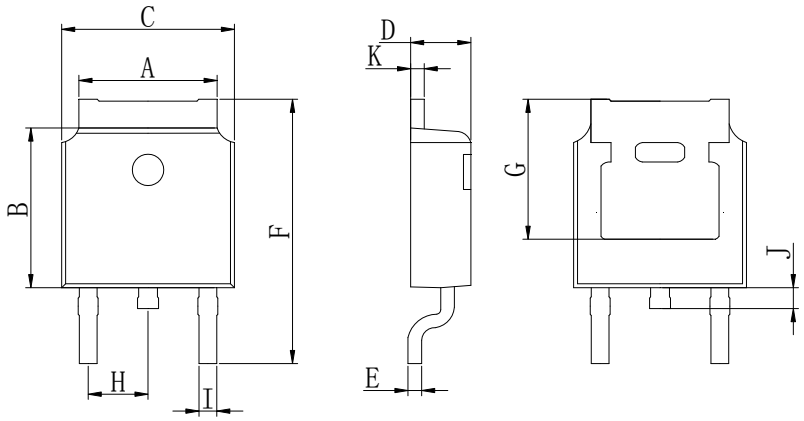
PACKAGE OUTLINE

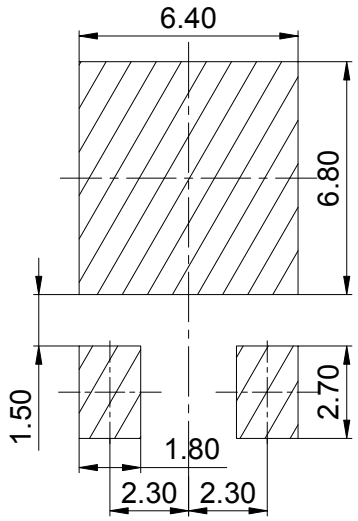
Plastic surface mounted package

TO-252



TO-252		
A	4.95	5.59
B	5.40	6.63
C	6.05	7.10
D	2.20	2.40
E	0.40	0.61
F	8.80	10.60
G	5.35 Typ.	
H	1.98	2.59
I	0.50	0.90
J	0.50	1.20
K	0.45	0.89
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit:mm

Power Transistor 2SD1760

PACKAGE INFORMATION

Device	Package	Shipping
2SD1760	TO-252	80PCS/Tube
		2500PCS/Tape&Reel